

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) Professional
PART NUMBER: OSWT5161A
MANUFACTURER: OPTO SUPPLY
REMARK: TA=25 degree C

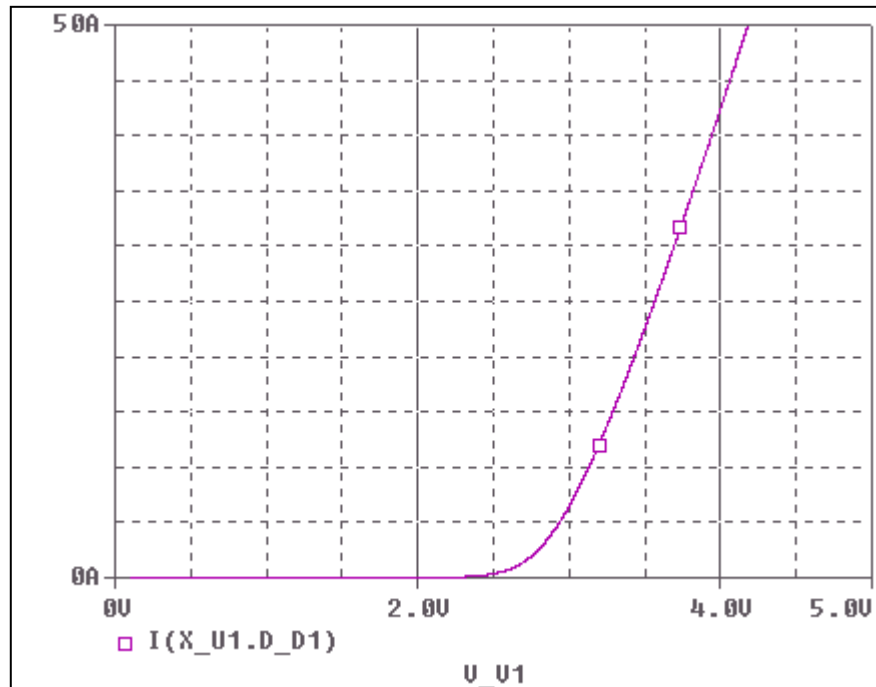


Bee Technologies Inc.

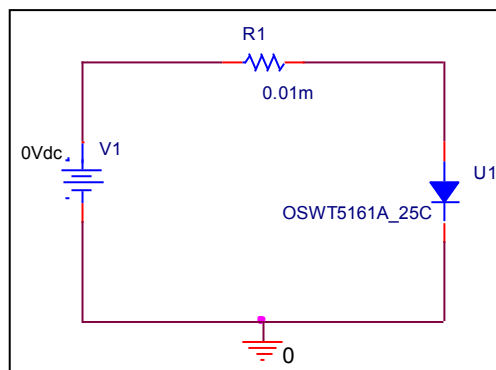
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

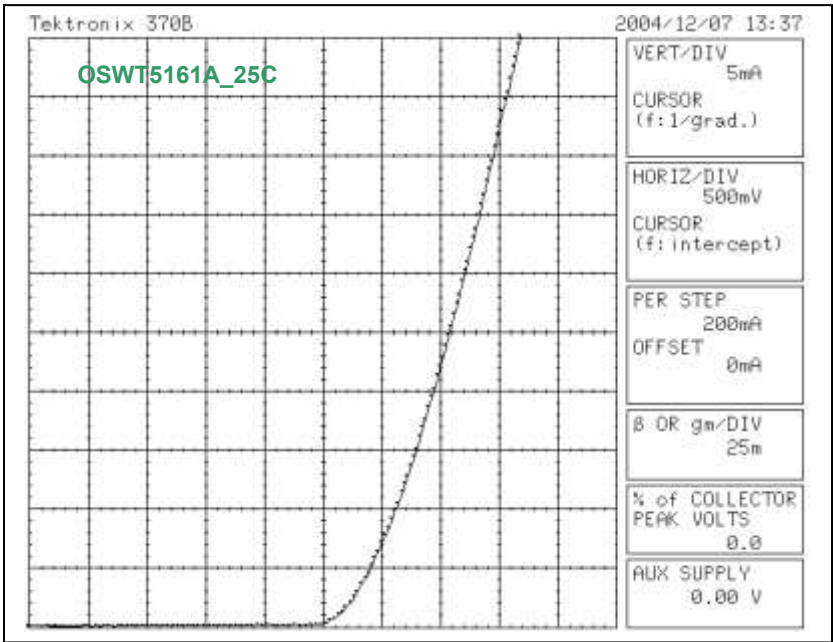


Evaluation Circuit



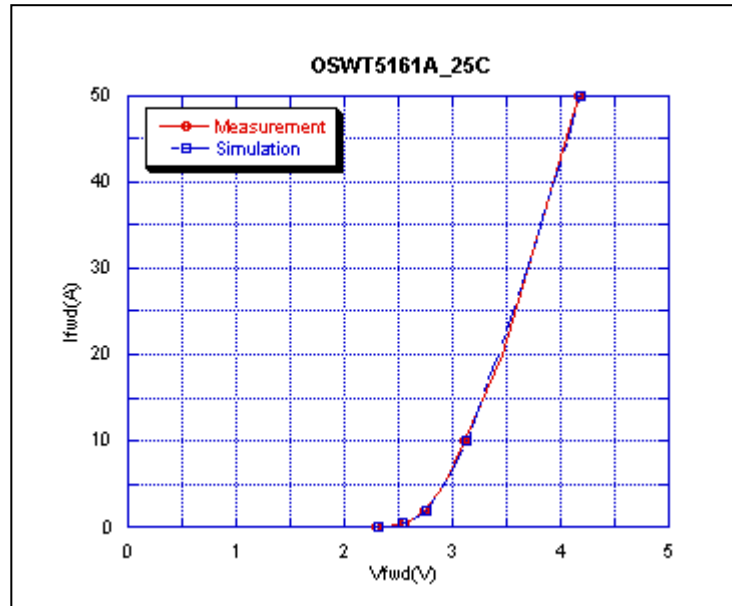
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

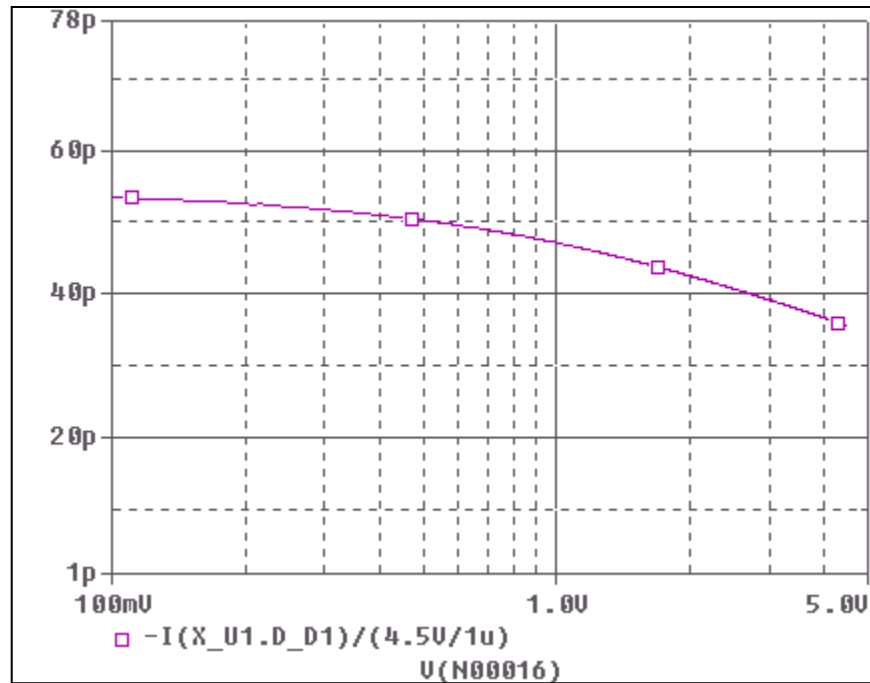


Simulation Result

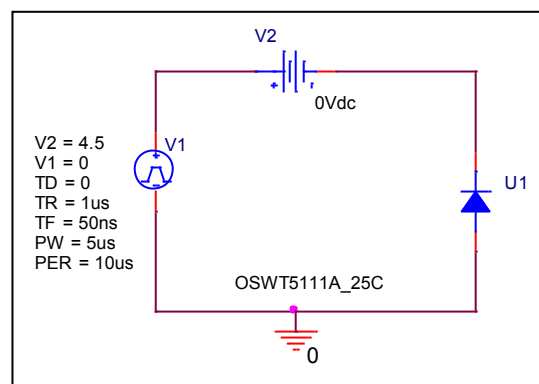
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
0.1	2.3	2.32	0.8695
0.2	2.45	2.42	1.2244
0.5	2.565	2.54	0.9746
1	2.645	2.644	0.0378
2	2.74	2.754	0.5109
5	2.925	2.935	0.3418
10	3.115	3.136	0.6741
20	3.455	3.43	0.7235
50	4.175	4.18	0.1197

Capacitance Characteristic

Circuit Simulation Result

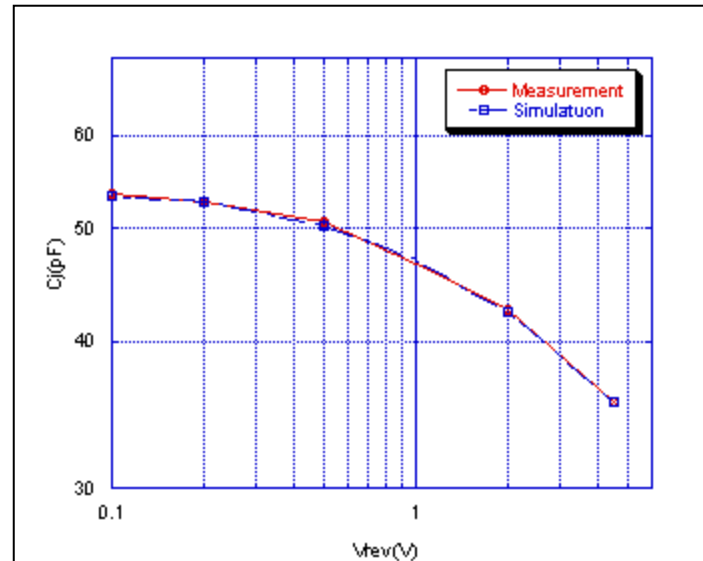


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

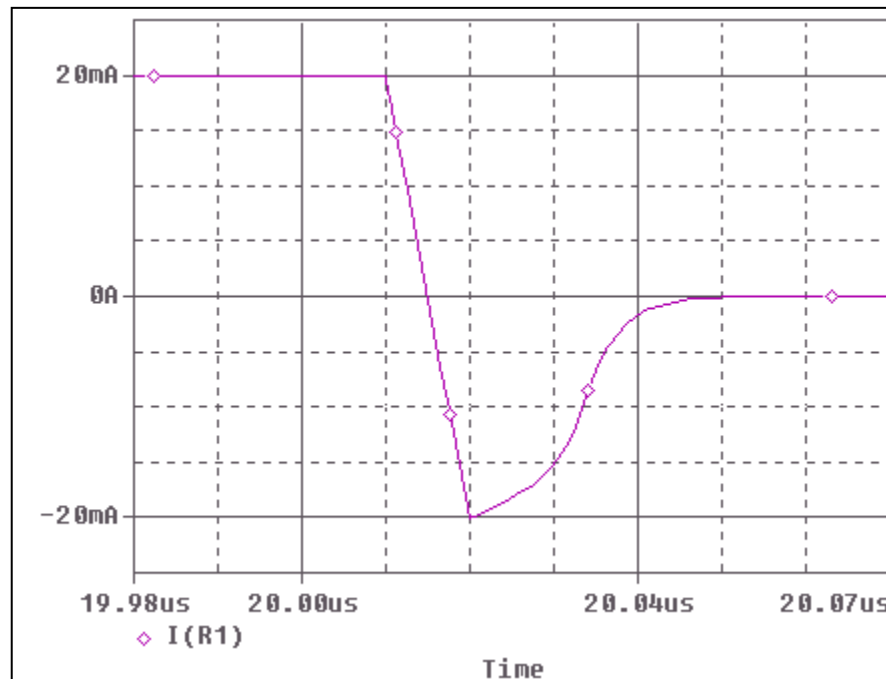


Simulation Result

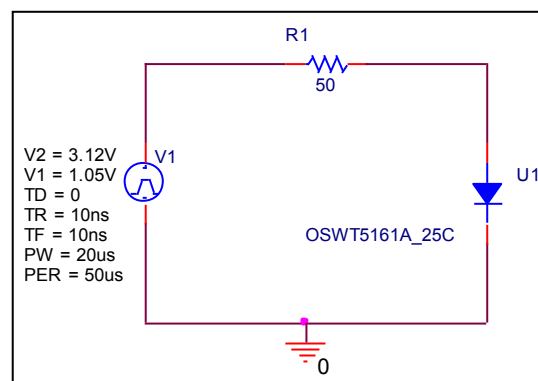
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	54.07	54.07	0
0.1	53.44	53.37	0.13098
0.2	52.78	52.577	0.38461
0.5	50.55	50.245	0.60336
1	46.68	47.006	0.69837
2	42.54	42.481	0.13869
4.5	35.59	35.583	0.01966

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

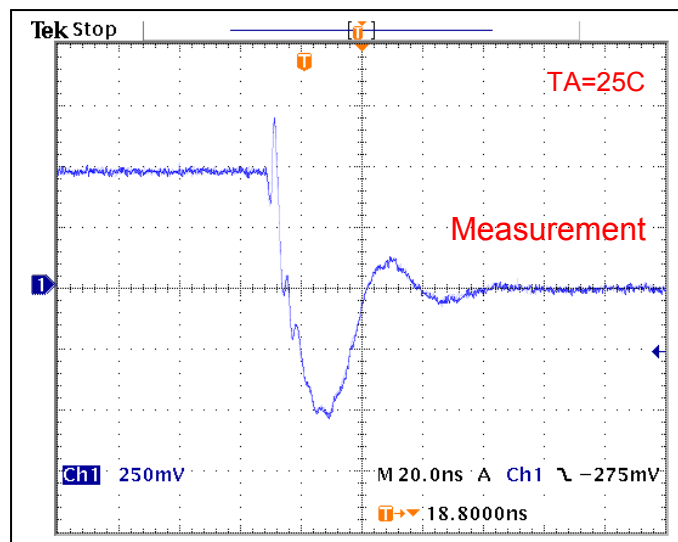


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
trj	12.4	ns	12.45	ns	0.05
trb	11.6	ns	11.58	ns	- 0.02

Reverse Recovery Characteristic

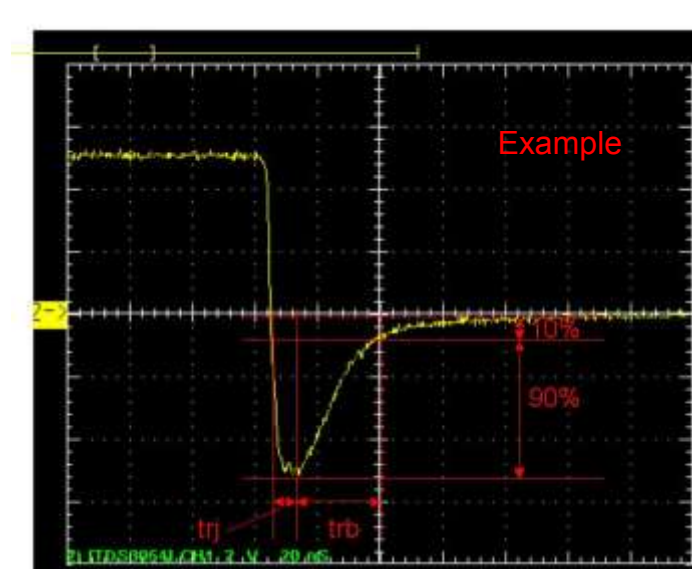
Reference



$\text{Trj} = 12.4\text{ns}$

$\text{Trb} = 11.6\text{ns}$

Conditions: $I_{\text{fwd}} = I_{\text{rev}} = 0.02\text{A}$, $R_I = 50$



Relation between trj and trb